Hiroshi Funakubo

List of Publications by Citations

665 papers	10,294 citations	46 h-index	76 g-index
707 ext. papers	11,219 ext. citations	2.3 avg, IF	6.05 L-index

#	Paper	IF	Citations
665	Dimensionality-controlled insulator-metal transition and correlated metallic state in 5d transition metal oxides Sr n+1Ir nO3n+1 (n=1, 2, and infinity). *Physical Review Letters*, **2008**, 101, 226402	7.4	354
664	Large remanent polarization of (Bi,Nd)4Ti3O12 epitaxial thin films grown by metalorganic chemical vapor deposition. *Applied Physics Letters*, **2002**, 80, 2746-2748	3.4	328
663	Stabilizing the ferroelectric phase in doped hafnium oxide. *Journal of Applied Physics*, **2015**, 118, 072006	2.5	294
662	Crystal structure and ferroelectric properties of rare-earth substituted BiFeO3 thin films. *Journal of Applied Physics*, **2006**, 100, 014106	2.5	215
661	High-□Dielectric Nanofilms Fabricated from Titania Nanosheets. *Advanced Materials*, **2006**, 18, 1023-1027	24	184
660	The demonstration of significant ferroelectricity in epitaxial Y-doped HfO2 film. *Scientific Reports*, **2016**, 6, 32931	4.9	153
659	Effect of cosubstitution of La and V in Bi4Ti3O12 thin films on the low-temperature deposition. *Applied Physics Letters*, **2002**, 80, 100-102	3.4	153
658	Approach for enhanced polarization of polycrystalline bismuth titanate films by Nd3+/V5+ cosubstitution. *Applied Physics Letters*, **2002**, 81, 2229-2231	3.4	149
657	Cation Distribution and Structural Instability in Bi4-xLaxTi3O12. *Japanese Journal of Applied Physics*, **2001**, 40, 5572-5575	1.4	143
656	Engineered interfaces of artificial perovskite oxide superlattices via nanosheet deposition process. *ACS Nano*, **2010**, 4, 6673-80	16.7	128
655	Robust high-□response in molecularly thin perovskite nanosheets. *ACS Nano*, **2010**, 4, 5225-32	16.7	125
654	Impact of mechanical stress on ferroelectricity in (Hf0.5Zr0.5)O2 thin films. *Applied Physics Letters*, **2016**, 108, 262904	3.4	121
653	Epitaxial BiFeO3 thin films fabricated by chemical solution deposition. *Applied Physics Letters*, **2006**, 88, 162904	3.4	108
652	Dependence of electrical properties of epitaxial Pb(Zr,Ti)O3 thick films on crystal orientation and Zr□(Zr+Ti) ratio. *Journal of Applied Physics*, **2005**, 98, 094106	2.5	105
651	Growth of epitaxial orthorhombic YO1.5-substituted HfO2 thin film. *Applied Physics Letters*, **2015**, 107, 032910	3.4	102
650	Preparation and characterization of a- and b-axis-oriented epitaxially grown Bi4Ti3O12-based thin films with long-range lattice matching. *Applied Physics Letters*, **2002**, 81, 1660-1662	3.4	94
649	Highly-conducting indium?tin-oxide transparent films fabricated by spray CVD using ethanol solution of indium (III) chloride and tin (II) chloride. *Thin Solid Films*, **2002**, 409, 46-50	2.2	91

648	Rhombohedral–Tetragonal Phase Boundary with High Curie Temperature in (1-x)BiCoO3–xBiFeO3Solid Solution. *Japanese Journal of Applied Physics*, **2008**, 47, 7579-7581	1.4	83
647	Ion Modification for Improvement of Insulating and Ferroelectric Properties of BiFeO3Thin Films Fabricated by Chemical Solution Deposition. *Japanese Journal of Applied Physics*, **2005**, 44, L561-L563	1.4	83
646	Large remanent polarization of Bi4Ti3O12-based thin films modified by the site engineering technique. *Journal of Applied Physics*, **2002**, 92, 1518-1521	2.5	82
645	Improvement of Property of Pb(ZrxTi1-x)O3 Thin Film Prepared by Source Gas Pulse-Introduced Metalorganic Chemical Vapor Deposition. *Japanese Journal of Applied Physics*, **2000**, 39, L996-L998	1.4	78
644	Electrical properties of (001)- and (116)-oriented epitaxial SrBi2Ta2O9 thin films prepared by metalorganic chemical vapor deposition. *Applied Physics Letters*, **1999**, 75, 1970-1972	3.4	78
643	Controlled crystal growth of layered-perovskite thin films as an approach to study their basic properties. *Journal of Applied Physics*, **2006**, 100, 051602	2.5	77
642	Origin of giant negative piezoelectricity in a layered van der Waals ferroelectric. *Science Advances*, **2019**, 5, eaav3780	14.3	74
641	Bi3-xMxTiTaO9(M = La or Nd) Ceramics with High Mechanical Quality FactorQm. *Japanese Journal of Applied Physics*, **2003**, 42, 6090-6093	1.4	71
640	Structural Characterization of BiFeO3Thin Films by Reciprocal Space Mapping. *Japanese Journal of Applied Physics*, **2006**, 45, 7311-7314	1.4	70
639	Film thickness dependence of ferroelectric properties of c-axis-oriented epitaxial Bi4Ti3O12 thin films prepared by metalorganic chemical vapor deposition. *Journal of Applied Physics*, **2001**, 89, 3934-3938	2.5	67
638	Controlled Polarizability of One-Nanometer-Thick Oxide Nanosheets for Tailored, High-κ Nanodielectrics. *Advanced Functional Materials*, **2011**, 21, 3482-3487	15.6	65
637	Composition and orientation dependence of electrical properties of epitaxial Pb(ZrxTi1−x)O3 thin films grown using metalorganic chemical vapor deposition. *Journal of Applied Physics*, **2004**, 95, 3111-3115	2.5	63
636	Large remanent polarization of 100% polar-axis-oriented epitaxial tetragonal Pb(Zr0.35Ti0.65)O3 thin films. *Applied Physics Letters*, **2003**, 82, 4761-4763	3.4	62
635	Fabrication of M3+-Substituted and M3+/V5+-Cosubstituted Bismuth Titanate Thin Films [M=lanthanoid] by Chemical Solution Deposition Technique. *Japanese Journal of Applied Physics*, **2002**, 41, 6820-6824	1.4	58
634	Effects of deposition conditions on the ferroelectric properties of (Al1−xScx)N thin films. *Journal of Applied Physics*, **2020**, 128, 114103	2.5	58
633	Analysis for crystal structure of Bi(Fe,Sc)O3 thin films and their electrical properties. *Applied Physics Letters*, **2007**, 91, 022906	3.4	56
632	Spontaneous polarization change with Zr/(Zr+Ti) ratios in perfectly polar-axis-orientated epitaxial tetragonal Pb(Zr,Ti)O3 films. *Applied Physics Letters*, **2004**, 85, 3516-3518	3.4	56
631	Contribution of oxygen vacancies to the ferroelectric behavior of Hf0.5Zr0.5O2 thin films. *Applied Physics Letters*, **2015**, 106, 112904	3.4	55

630	Structural characterization and 90□domain contribution to ferroelectricity of epitaxial Pb(Zr0.35,Ti0.65)O3 thin films. *Journal of Applied Physics*, **2003**, 93, 545-550	2.5	55
629	Low-Temperature Deposition of SrRuO3Thin Film Prepared by Metalorganic Chemical Vapor Deposition. *Japanese Journal of Applied Physics*, **2000**, 39, 572-576	1.4	54
628	Growth of (111)-oriented epitaxial and textured ferroelectric Y-doped HfO2 films for downscaled devices. *Applied Physics Letters*, **2016**, 109, 112901	3.4	54
627	Ferroelectric properties of lanthanide-substituted Bi4Ti3O12 epitaxial thin films grown by metalorganic chemical vapor deposition. *Journal of Applied Physics*, **2003**, 93, 1707-1712	2.5	50
626	Crystal Structure and Electrical Properties of Epitaxial BiFeO3Thin Films Grown by Metal Organic Chemical Vapor Deposition. *Japanese Journal of Applied Physics*, **2005**, 44, L1231-L1233	1.4	50
625	Method of Distinguishing SrBi2Ta2O9Phase from Fluorite Phase Using X-Ray Diffraction Reciprocal Space Mapping. *Japanese Journal of Applied Physics*, **2000**, 39, 5489-5495	1.4	49
624	Orientation dependence of ferroelectricity of epitaxially grown Pb(ZrxTi1□)O3 thin films prepared by metalorganic chemical vapor deposition. *Journal of Applied Physics*, **2001**, 89, 4517-4522	2.5	49
623	Film Thickness Dependence of Dielectric Property and Crystal Structure of PbTiO3Film Prepared on Pt/SiO2/Si Substrate by Metal Organic Chemical Vapor Deposition. *Japanese Journal of Applied Physics*, **1993**, 32, 4175-4178	1.4	49
622	Ferroelectricity mediated by ferroelastic domain switching in HfO2-based epitaxial thin films. *Applied Physics Letters*, **2018**, 113, 212901	3.4	49
621	Ferroelectric properties of an epitaxial lead zirconate titanate thin film deposited by a hydrothermal method below the Curie temperature. *Applied Physics Letters*, **2004**, 84, 5094-5096	3.4	47
620	Composition Control of Pb(ZrxTi1-x)O3Thin Films Prepared by Metalorganic Chemical Vapor Deposition. *Japanese Journal of Applied Physics*, **2000**, 39, 212-216	1.4	47
619	Dependence of Ferroelectric Properties on Thickness of BiFeO3Thin Films Fabricated by Chemical Solution Deposition. *Japanese Journal of Applied Physics*, **2005**, 44, 8525-8527	1.4	45
618	Crystal Structure Analysis of Epitaxial BiFeO3□BiCoO3Solid Solution Films Grown by Metalorganic Chemical Vapor Deposition. *Japanese Journal of Applied Physics*, **2007**, 46, 6948-6951	1.4	44
617	Ruthenium Film with High Nuclear Density Deposited by MOCVD Using a Novel Liquid Precursor. *Electrochemical and Solid-State Letters*, **2003**, 6, C117		43
616	Fabrication of ZnO Microstructures by Anisotropic Wet-Chemical Etching. *Journal of the Electrochemical Society*, **2007**, 154, D82	3.9	42
615	Ferroelectric property of epitaxial Bi4Ti3O12 films prepared by metalorganic chemical vapor deposition. *Journal of Materials Research*, **2001**, 16, 303-307	2.5	42
614	Orientation control and domain structure analysis of {100}-oriented epitaxial ferroelectric orthorhombic HfO2-based thin films. *Journal of Applied Physics*, **2016**, 119, 134101	2.5	42
613	Effect of Strain in Epitaxially Grown SrRuO3Thin Films on Crystal Structure and Electric Properties. *Japanese Journal of Applied Physics*, **2002**, 41, 5376-5380	1.4	41

612	Epitaxial PZT films for MEMS printing applications. *MRS Bulletin*, **2012**, 37, 1030-1038	3.2	40
611	Fatigue-free RuO2/Pb(Zr,Ti)O3/RuO2 capacitor prepared by metalorganic chemical vapor deposition at 395 °C. *Applied Physics Letters*, **2003**, 83, 5506-5508	3.4	40
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605	Configuration and local elastic interaction of ferroelectric domains and misfit dislocation in PbTiO/SrTiO epitaxial thin films. *Science and Technology of Advanced Materials*, **2011**, 12, 034413	7.1	37
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603	RF Magnetron Sputtering Growth of Epitaxial SrRuO3Films with High Conductivity. *Japanese Journal of Applied Physics*, **2007**, 46, 6987-6990	1.4	37
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600	Thickness dependence of dielectric properties in bismuth layer-structured dielectrics. *Applied Physics Letters*, **2006**, 89, 082901	3.4	36
599	Room-temperature epitaxial growth of indium tin oxide thin films on Si substrates with an epitaxial CeO2 ultrathin buffer. *Thin Solid Films*, **2002**, 415, 272-275	2.2	36
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597	Crystal structure and electrical properties of epitaxial SrBi2Ta2O9 films. *Journal of Applied Physics*, **2000**, 87, 8018-8023	2.5	35
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593	Metalorganic Chemical Vapor Deposition of Epitaxial Perovskite SrIrO3Films on (100)SrTiO3Substrates. *Japanese Journal of Applied Physics*, **2006**, 45, L36-L38	1.4	33
592	Property design of Bi4Ti3O12-based thin films using a site-engineered concept. *Journal of Crystal Growth*, **2003**, 248, 180-185	1.6	33
591	Transport properties and c/a ratio of V2O3 thin films grown on C- and R-plane sapphire substrates by pulsed laser deposition. *Applied Physics Letters*, **2015**, 107, 241901	3.4	32
590	Crystal structure, electrical properties, and mechanical response of (100)-/(001)-oriented epitaxial Pb(Mg1⁄3Nb2⁄3)O3–PbTiO3 films grown on (100)cSrRuO3?(100)SrTiO3 substrates by metal-organic chemical vapor deposition. *Journal of Applied Physics*, **2006**, 100, 054110	2.5	32
589	Large piezoelectric response in (111)-oriented epitaxial Pb(Zr,Ti)O3 films consisting of mixed phases with rhombohedral and tetragonal symmetry. *Applied Physics Letters*, **2003**, 83, 2408-2410	3.4	32
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587	Laser Wavelength Effect on Size and Morphology of Silicon Nanoparticles Prepared by Laser Ablation in Liquid. *Japanese Journal of Applied Physics*, **2013**, 52, 025001	1.4	31
586	Preparation of Pb(Zrx, Ti1-x)O3Thin Films by Source Gas Pulse-Introduced Metalorganic Chemical Vapor Deposition. *Japanese Journal of Applied Physics*, **2001**, 40, 4126-4130	1.4	31
585	Enhancement of ferroelectric and magnetic properties in BiFeO3 films by small amount of cobalt addition. *Journal of Applied Physics*, **2008**, 103, 07E314	2.5	30
584	Strain-relaxed structure in (001)–(100)-oriented epitaxial PbTiO3 films grown on (100) SrTiO3 substrates by metal organic chemical vapor deposition. *Applied Physics Letters*, **2007**, 91, 112904	3.4	30
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581	Dynamic piezoresponse force microscopy: Spatially resolved probing of polarization dynamics in time and voltage domains. *Journal of Applied Physics*, **2012**, 112, 052021	2.5	28
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579	The Influence of Acceptor Doping on the Structure and Electrical Properties of Sol-Gel Derived BiFeO3 Thin Films. *Ferroelectrics*, **2007**, 357, 35-40	0.6	27
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575	Orientation Dependence of Epitaxial and One-Axis-Oriented (Ba0.5Sr0.5)TiO3Films Prepared by RF Magnetron Sputtering. *Japanese Journal of Applied Physics*, **2005**, 44, 6881-6884	1.4	27
574	Suppressed polar distortion with enhanced Curie temperature in in-plane 90°-domain structure of a-axis oriented PbTiO3 Film. *Applied Physics Letters*, **2015**, 106, 042905	3.4	26
573	Seed Layer Free Conformal Ruthenium Film Deposition on Hole Substrates by MOCVD Using (2,4-Dimethylpentadienyl)(ethylcyclopentadienyl)ruthenium. *Electrochemical and Solid-State Letters* , **2006**, 9, C107		26
572	Low-Temperature Preparation of Metallic Ruthenium Films by MOCVD Using Bis(2,4-dimethylpentadienyl)ruthenium. *Electrochemical and Solid-State Letters*, **2007**, 10, D60		26
571	Domain structure of (100)/(001)-oriented epitaxial PbTiO3 thick films with various volume fraction of (001) orientation grown by metal organic chemical vapor deposition. *Applied Physics Letters*, **2009**, 94, 052906	3.4	25
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569	Preparation of SrBi2Ta2O9 Thin Films by Metalorganic Chemical Vapor Deposition from Two New Liquid Organometallic Sources. *Japanese Journal of Applied Physics*, **1999**, 38, L199-L201	1.4	25
568	Measurement of transient photoabsorption and photocurrent of BiFeO3 thin films: Evidence for long-lived trapped photocarriers. *Physical Review B*, **2014**, 89,	3.3	24
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565	Low Temperature Deposition of Pb(Zr,Ti)O3 Film by Source Gas Pulse-Introduced Metalorganic Chemical Vapor Deposition. *Japanese Journal of Applied Physics*, **2001**, 40, L343-L345	1.4	24
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556	Preparation and characterization of Pb(Nb,Ti)O3 thin films by metalorganic chemical vapor deposition. *Journal of Applied Physics*, **1999**, 86, 4559-4564	2.5	23
555	Residual Strain and Crystal Structure ofBaTiO3SrTiO3Thin Films Prepared by Metal Organic Chemical Vapor Deposition. *Japanese Journal of Applied Physics*, **1997**, 36, 5879-5884	1.4	22
554	1.54h photoluminescence from FeSi2 as-deposited film. *Applied Physics Letters*, **2007**, 91, 071903	3.4	22
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551	MOCVD growth of epitaxial SrIrO3 films on (111)SrTiO3 substrates. *Thin Solid Films*, **2005**, 486, 182-185	2.2	22
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541	Photocatalytic hydrogen evolution over ron silicide under infrared-light irradiation. *Chemical Communications*, **2015**, 51, 2818-20	5.8	20

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532	Effects of heat treatment and in situ high-temperature X-ray diffraction study on the formation of ferroelectric epitaxial Y-doped HfO2 film. *Japanese Journal of Applied Physics*, **2019**, 58, SBBB09	1.4	19
531	In-situ observation of ultrafast 90° domain switching under application of an electric field in (100)/(001)-oriented tetragonal epitaxial Pb(ZrTi)O thin films. *Scientific Reports*, **2017**, 7, 9641	4.9	19
530	Interface control of a morphotropic phase boundary in epitaxial samarium modified bismuth ferrite superlattices. *Physical Review B*, **2014**, 90,	3.3	19
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528	Crystal Structure Analysis of Hydrothermally Synthesized Epitaxial (KxNa1-x)NbO3Films. *Japanese Journal of Applied Physics*, **2013**, 52, 09KA11	1.4	19
527	Annealing Temperature Dependences of Ferroelectric and Magnetic Properties in Polycrystalline Co-Substituted BiFeO3Films. *Japanese Journal of Applied Physics*, **2008**, 47, 7574-7578	1.4	19
526	Experimental evidence of strain relaxed domain structure in (100)/(001)-oriented epitaxial lead titanate thick films grown by metal organic chemical vapor deposition. *Journal of Applied Physics*, **2008**, 104, 064121	2.5	19
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524	Effect of Oxygen Annealing on Ferroelectricity of BiFeO3Thin Films Formed by Pulsed Laser Deposition. *Japanese Journal of Applied Physics*, **2007**, 46, 3491-3494	1.4	19
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